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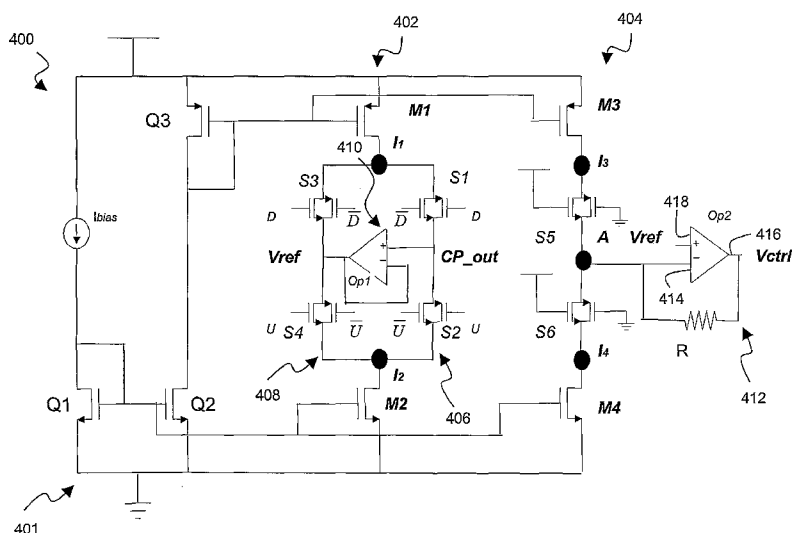
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(54) Title: A CHARGE PUMP CIRCUIT



(57) Abstract: A charge pump circuit and a method of compensating current mismatch in a charge pump circuit. The charge pump circuit comprises a core charge pump circuit; a replica charge pump circuit for sensing a current mismatch in the core charge pump circuit and for converting the sensed current mismatch into a voltage signal V_ctrl; wherein V_ctrl is utilised for compensating the current mismatch in the core charge pump circuit.